

NCE8290

## NCE N-Channel Enhancement Mode Power MOSFET

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## **Description**

The NCE8290 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

#### **General Features**

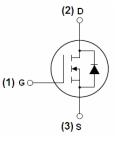
- $V_{DS}$  = 82V, $I_{D}$  =90A  $R_{DS(ON)}$  < 8.5mΩ @  $V_{GS}$ =10V (Typ:7.5mΩ)
- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E<sub>AS</sub>
- Excellent package for good heat dissipation

## **Application**

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% AVds TESTED!



Schematic diagram



Marking and pin assignment



TO-220-3L top view

## **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE8290	NCE8290	TO-220-3L	-	-	-

## Absolute Maximum Ratings (T<sub>C</sub>=25<sup>°</sup>Cunless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	82	V	
Gate-Source Voltage	V <sub>G</sub> S	±20	V	
Drain Current-Continuous	I <sub>D</sub>	90	А	
Drain Current-Continuous(T <sub>C</sub> =100℃)	I <sub>D</sub> (100℃)	63	Α	
Pulsed Drain Current	I <sub>DM</sub>	320	Α	
Maximum Power Dissipation	P <sub>D</sub>	170	W	



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Derating factor		1.13	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	550	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^{\circ}$

## **Thermal Characteristic**

Thermal Resistance, Junction-to-Case (Note 2)	R <sub>θJc</sub>	0.88	°C/W	
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## **Electrical Characteristics (Tc=25** ℃ unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	<u>.</u>					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	82	85	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =75V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)	<u>.</u>					
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	2	2.9	4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =40A	-	7.5	8.5	mΩ
Forward Transconductance	<b>g</b> Fs	V <sub>DS</sub> =10V,I <sub>D</sub> =40A	-	50	-	S
Dynamic Characteristics (Note4)	<u>.</u>					
Gate resistance	Rg	V <sub>DS</sub> =0V,V <sub>GS</sub> =0V,F=1.0MHz	-	0.63	-	Ω
Input Capacitance	C <sub>lss</sub>	\/ -45\/\/ -0\/	-	4871	-	PF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =15V, $V_{GS}$ =0V, F=1.0MHz	-	630.6	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UIVITZ	-	410.3	-	PF
Switching Characteristics (Note 4)	<u>.</u>					
Turn-on Delay Time	t <sub>d(on)</sub>		-	36.1	-	nS
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> =30V,I <sub>D</sub> =42A	-	54.3	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{GEN}$ =10 $\Omega$	-	85.2	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	37.3	-	nS
Total Gate Charge	Qg	\/ 40\/   044	-	85.7	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ =48V, $I_{D}$ =84A, $V_{GS}$ =10V	-	23.2	-	nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	31.2	-	nC
Drain-Source Diode Characteristics	<u>.</u>					
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =20A	-	-	1.2	V
Diode Forward Current (Note 2)	Is	-	-	-	90	Α
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF =84A	-	88.3	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	65.9	-	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

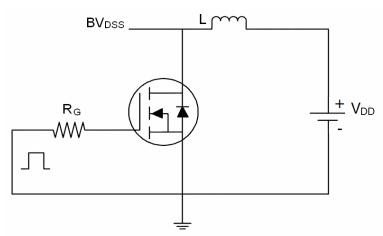
## Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25  $^{\circ}$ C,V<sub>DD</sub>=40V,V<sub>G</sub>=10V,L=0.5mH,Rg=25 $\Omega$

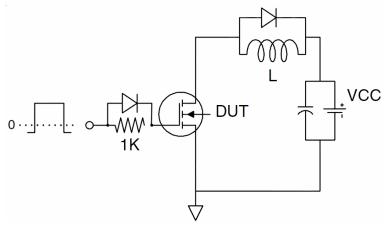


## **Test circuit**

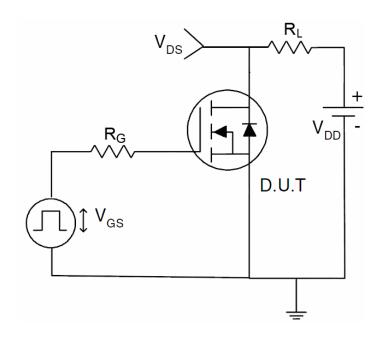
## 1) E<sub>AS</sub> test Circuits



## 2) Gate charge test Circuit:



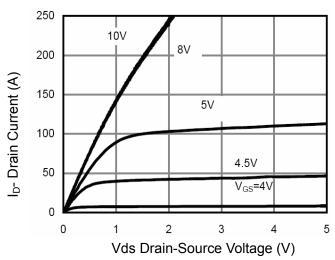
## 3) Switch Time Test Circuit:



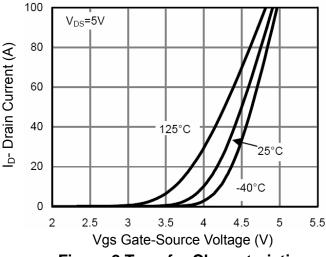


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## **Typical Electrical and Thermal Characteristics (Curves)**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

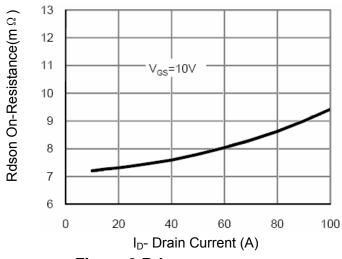


Figure 3 Rdson- Drain Current

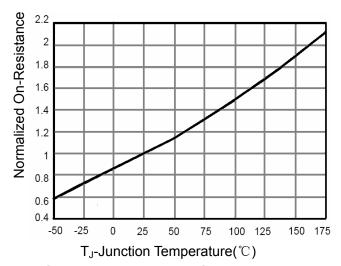


Figure 4 Rdson-JunctionTemperature

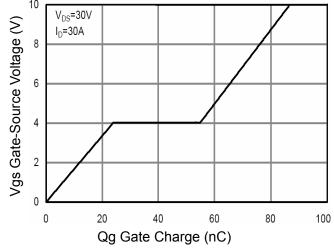


Figure 5 Gate Charge

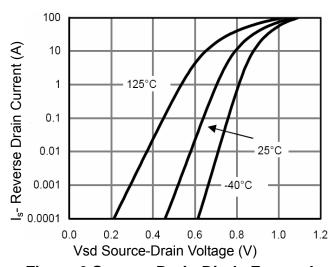


Figure 6 Source- Drain Diode Forward



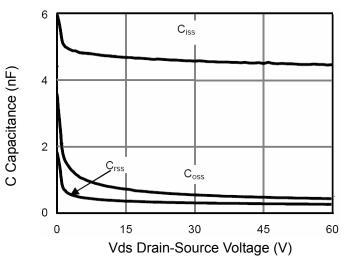
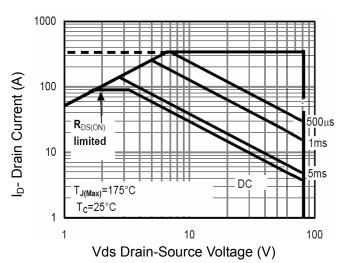


Figure 7 Capacitance vs Vds



**Figure 8 Safe Operation Area** 

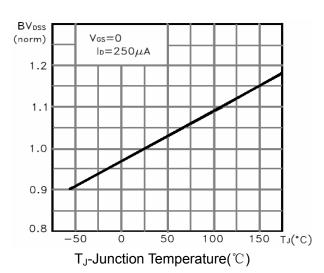


Figure 9 BV<sub>DSS</sub> vs Junction Temperature

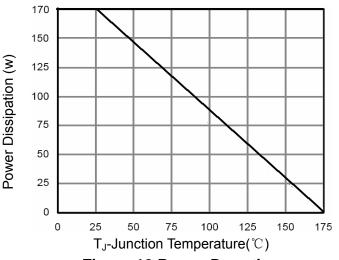
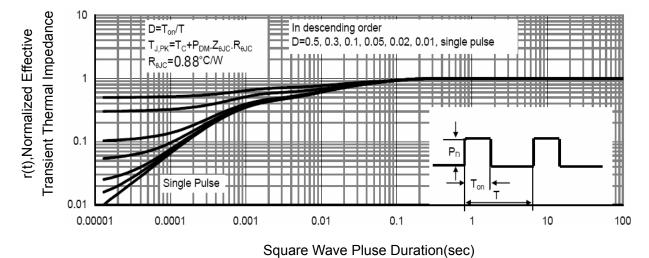


Figure 10 Power De-rating



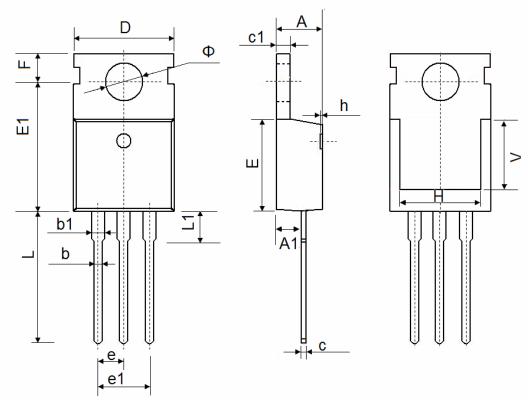
**Figure 11 Normalized Maximum Transient Thermal Impedance** 

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## **TO-220-3L Package Information**



Compleal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295	REF.	
Ф	3.400	3.800	0.134	0.150	



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